

# **MEMS based sensors for indoor environment applications**

Ralph W. Bernstein, Niels-Peter Østbø

*SINTEF ICT*

Bertil Høk

*Høk Instruments*

Per G. Gløersen

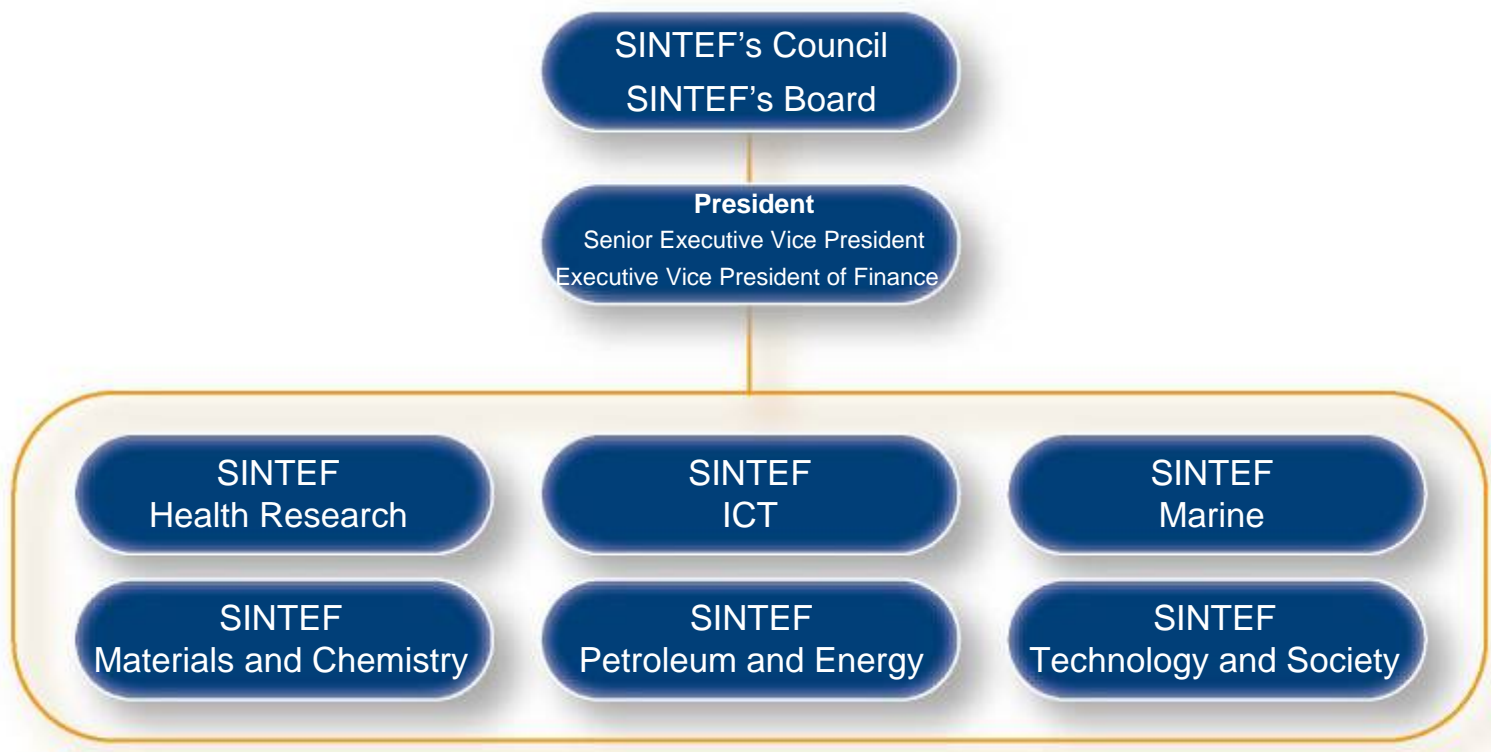
*SensoNor ASA*



TEF



# The SINTEF Group



# MiNaLab (Micro Nano Lab)



- Clean room area:  
SINTEF: 800 m<sup>2</sup>  
University of Oslo: 600 m<sup>2</sup>
- Micro environments, class 10
- A full silicon processing line for MEMS and radiation detectors
- Capacity of 10.000 6" wafers/year
- 35 employees at SINTEF
- Located at the campus of University of Oslo
- 240 MNOK invested in scientific equipment and laboratory infrastructure
- Funded by Norwegian Research Council and SINTEF

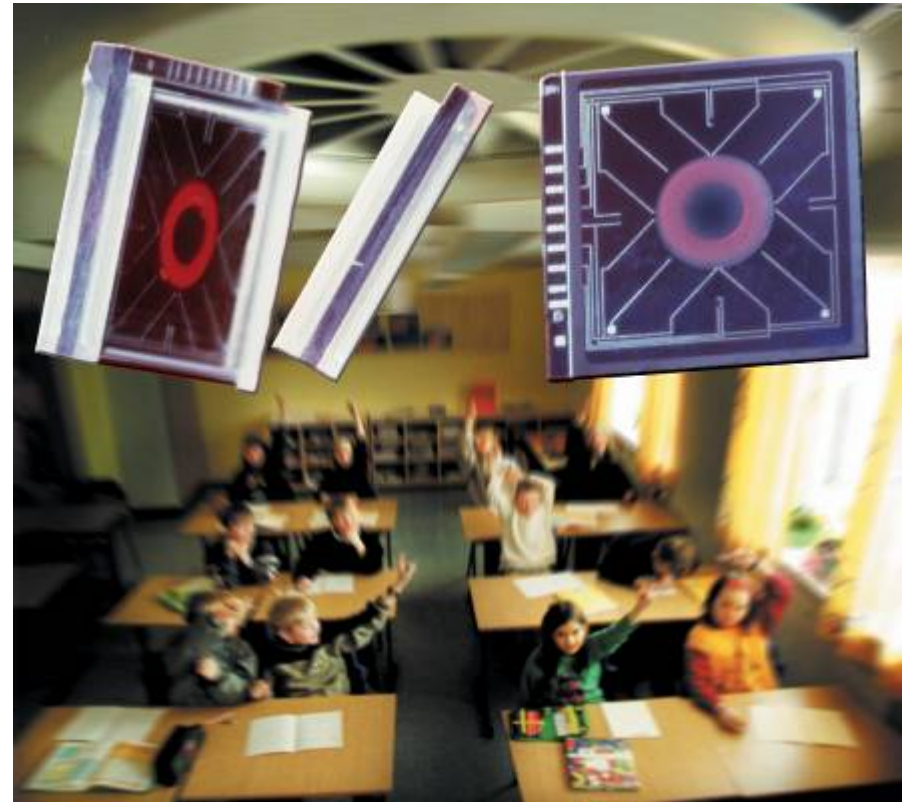
## MiNaLab offer

- One of two silicon processing lines in Norway. The only *independent one*.
- Offers the complete range from *design, process and device development through flexible prototyping and production*.
  
- **Production:**
  - Contract production of MEMS using processes not commercial available in industrial foundries.
  - Contract and foundry production of radiation detectors.
- **MEMS design center:**
  - SensoNor process = MULTIMEMS
  - Other available foundry processes
  - In-house MEMS processes

# Key parameters for IAQ control

- Temperature
- CO<sub>2</sub>
- Humidity
- Other gases (e.g. CO)

There is a strong demand for (networks of) low cost multi sensors



# Infrared (IR) gas sensing

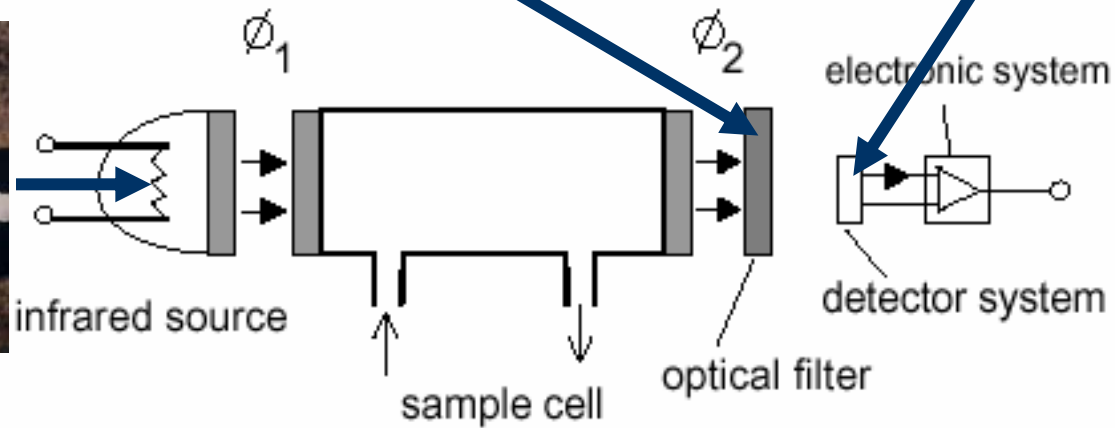
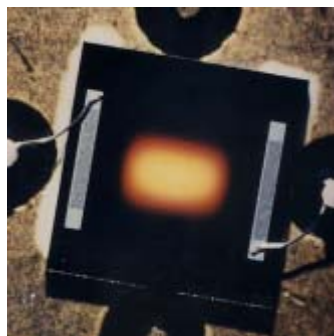
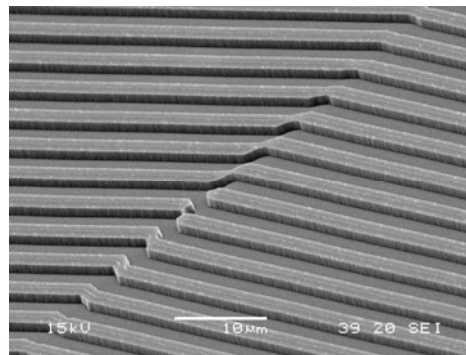
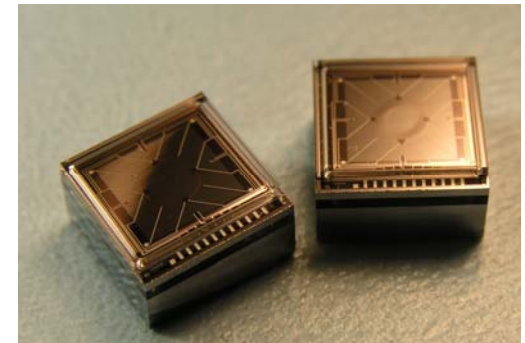
## Advantages:

- Selective
- Sensitive
- Non contact
- Reliable

## Disadvantages:

- Inherently expensive (at least two components)
- Large size
- Requires drift compensation
- Complex packaging

# MEMS devices for infrared gas sensing



## Micro ElectroMechanical Systems (MEMS)

Miniaturized systems that carry out several operations.  
Typically: sensing, signal conditioning and actuation

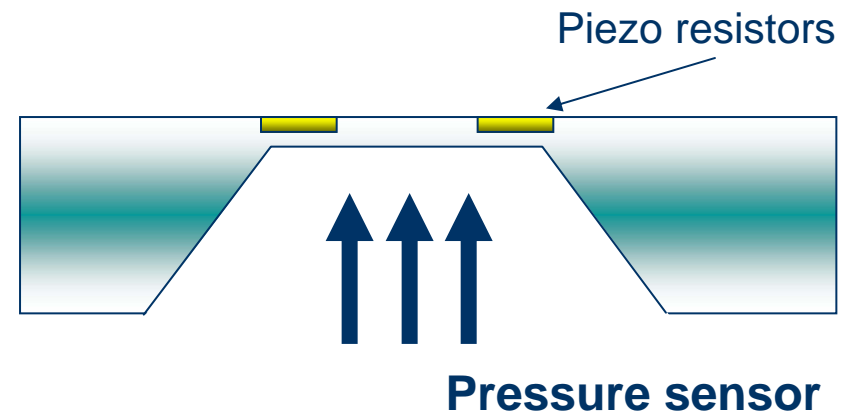
- **Micro sensor and/or actuator**
- **ASIC**
- **Packaging**





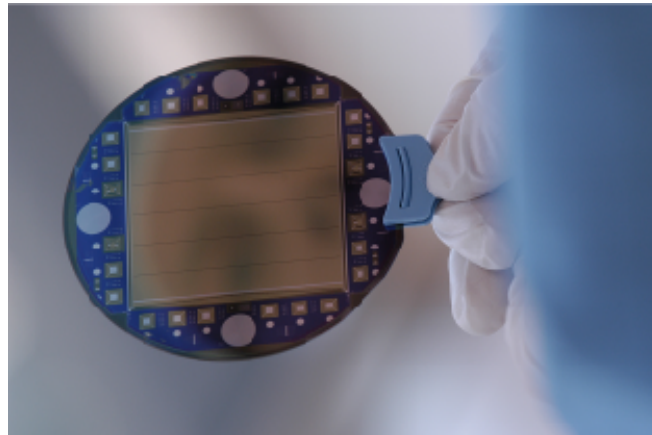
# Microsystem technology

- Utilizes the production technology developed for microelectronics to make sensors (**MEMS**)
  - Miniaturization
  - High volume, low cost production
  - Integration with electronics
  
- Special processes
  - Micromachining
  - Functional thin films
  - Wafer stacking



# Why silicon technology

- Batch processing => low cost, high volume
- Well established production technology
- Advanced infrastructure, materials and design tools available
- Wide range of sensor principles available
- Silicon has attractive mechanical properties
- Integration is possible

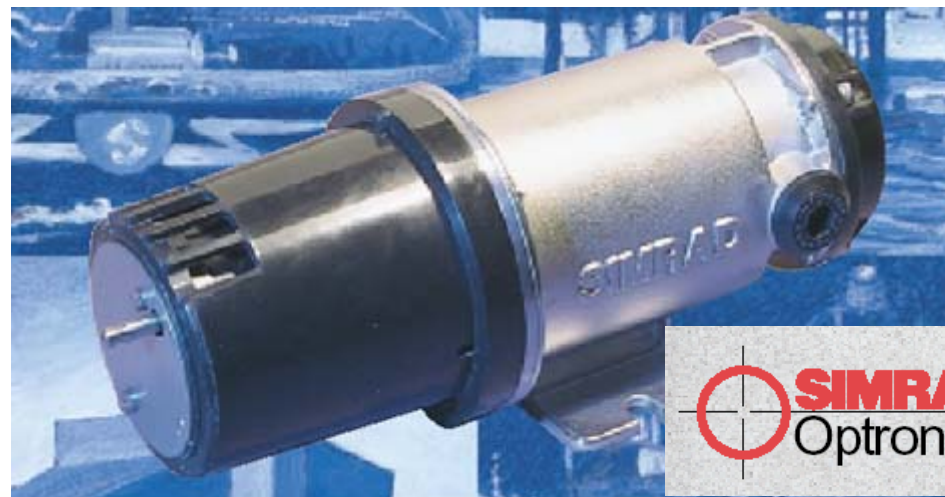
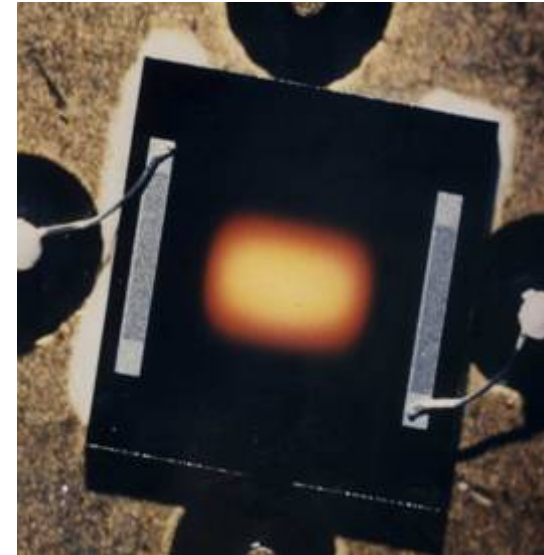


# IR sources

- Thermal sources
  - Conventional “light bulbs”
  - MEMS based IR sources
- IR LEDs
- IR LASERS

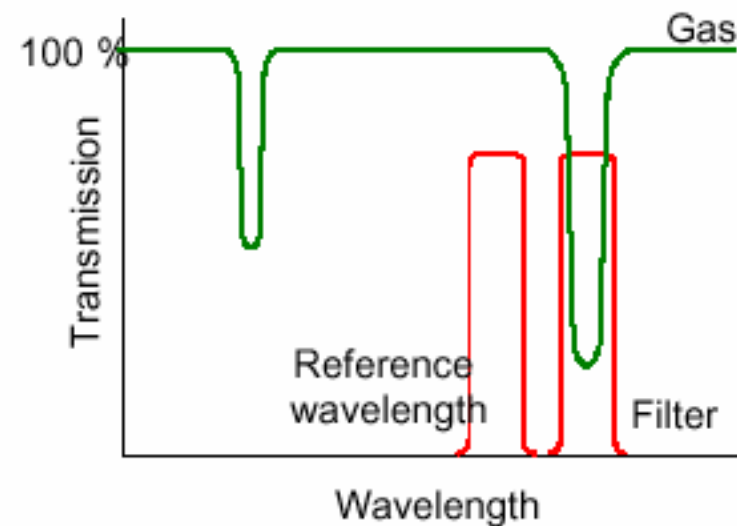
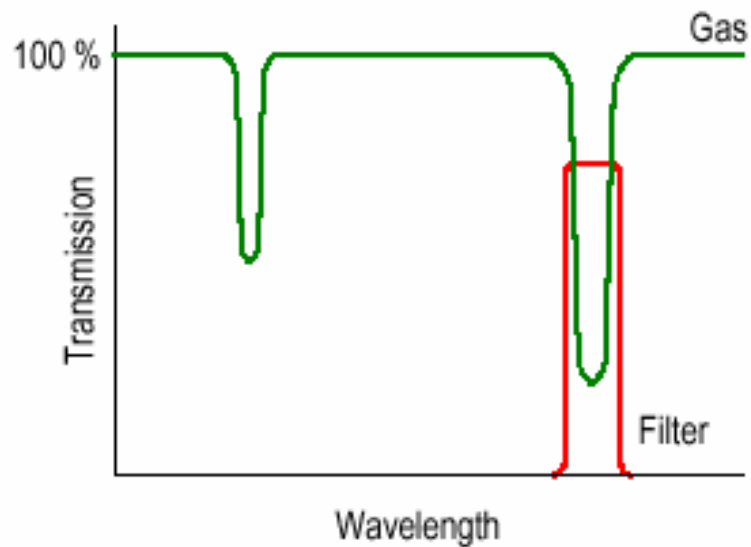
# The SINTEF infrared emitter

- Produced by silicon micromachining
- Grey body spectrum
- Electronically controlled modulation
- Modulation depth: 20 % @ 50 Hz
- Power consumption: ~ 1 Watt
- Application example:  
SIMRAD Optronics Gas Detector  
for methane (CH<sub>4</sub>)  
More than 15 years of  
continuous operation  
in the North Sea

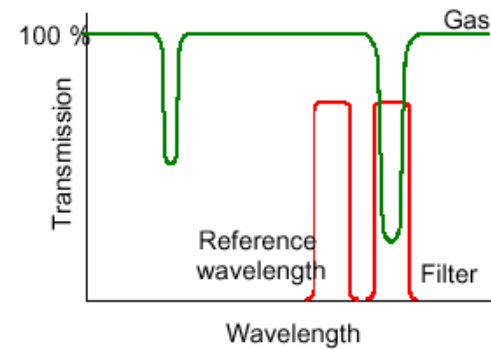
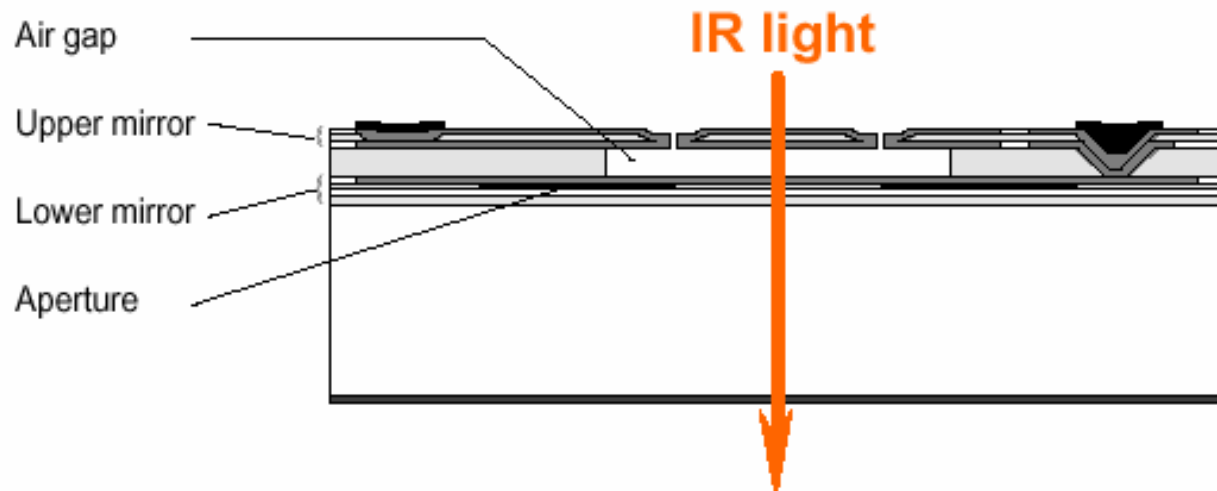


# Filters

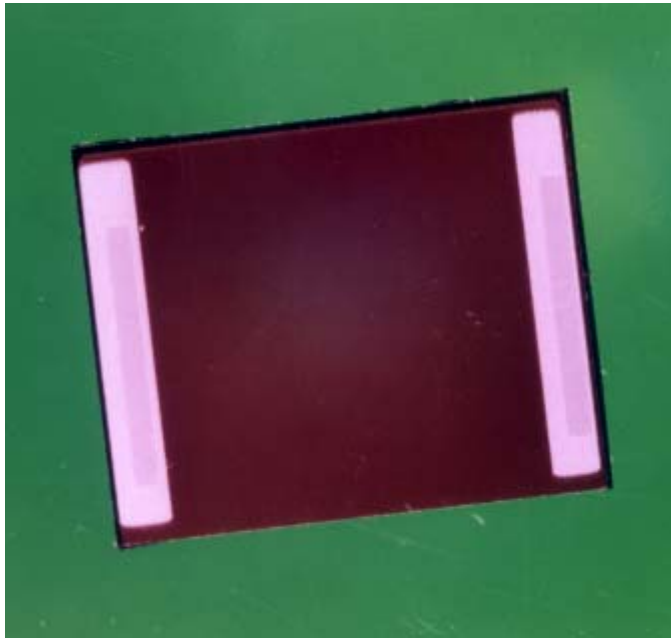
- Single gas selectivity
- Compensation
- Multi gas detection (CO, humidity)



# The Carbocap<sup>®</sup> technology from VAISALA

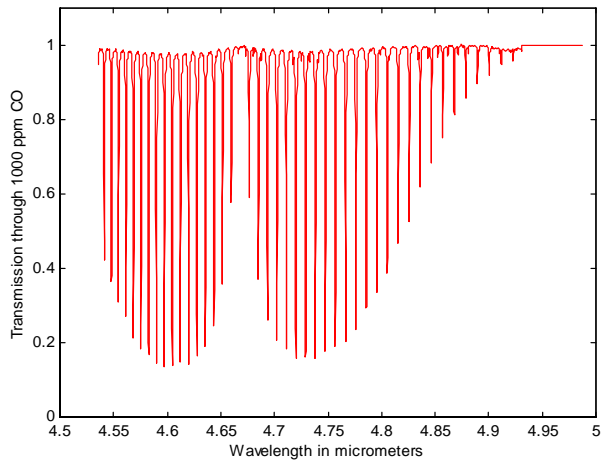


## A CO and methane sensor based on a thermally tuned Fabry-Perot filter



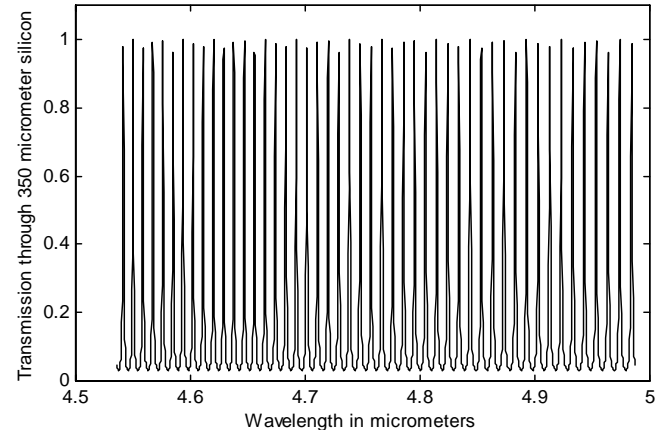
- Micromachined in silicon
- Based on the thermo-opto effect  
 $\Delta T \sim 25^\circ \text{C}$
- Designed to synthesize a characteristic gas spectrum
- Electrically modulated 10 nm
- Wavelengths from  $1.2 \mu\text{m}$  ->
- Modulation frequency: 1 Hz
- Simple design, low cost

Rogne, Bernstein, Avset, Ferber, and Johansen  
MOEMS '99, Heidelberg

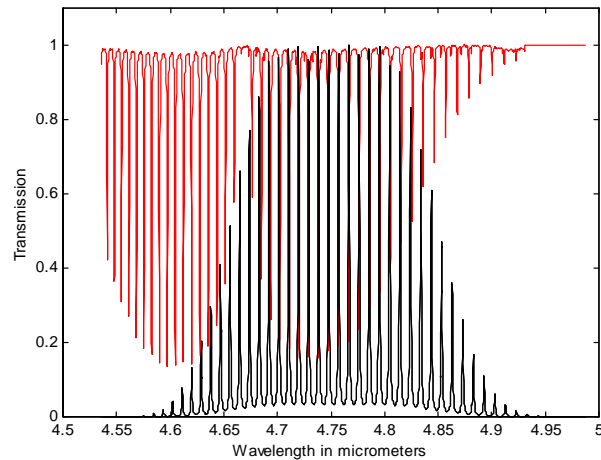


CO absorption pattern

+

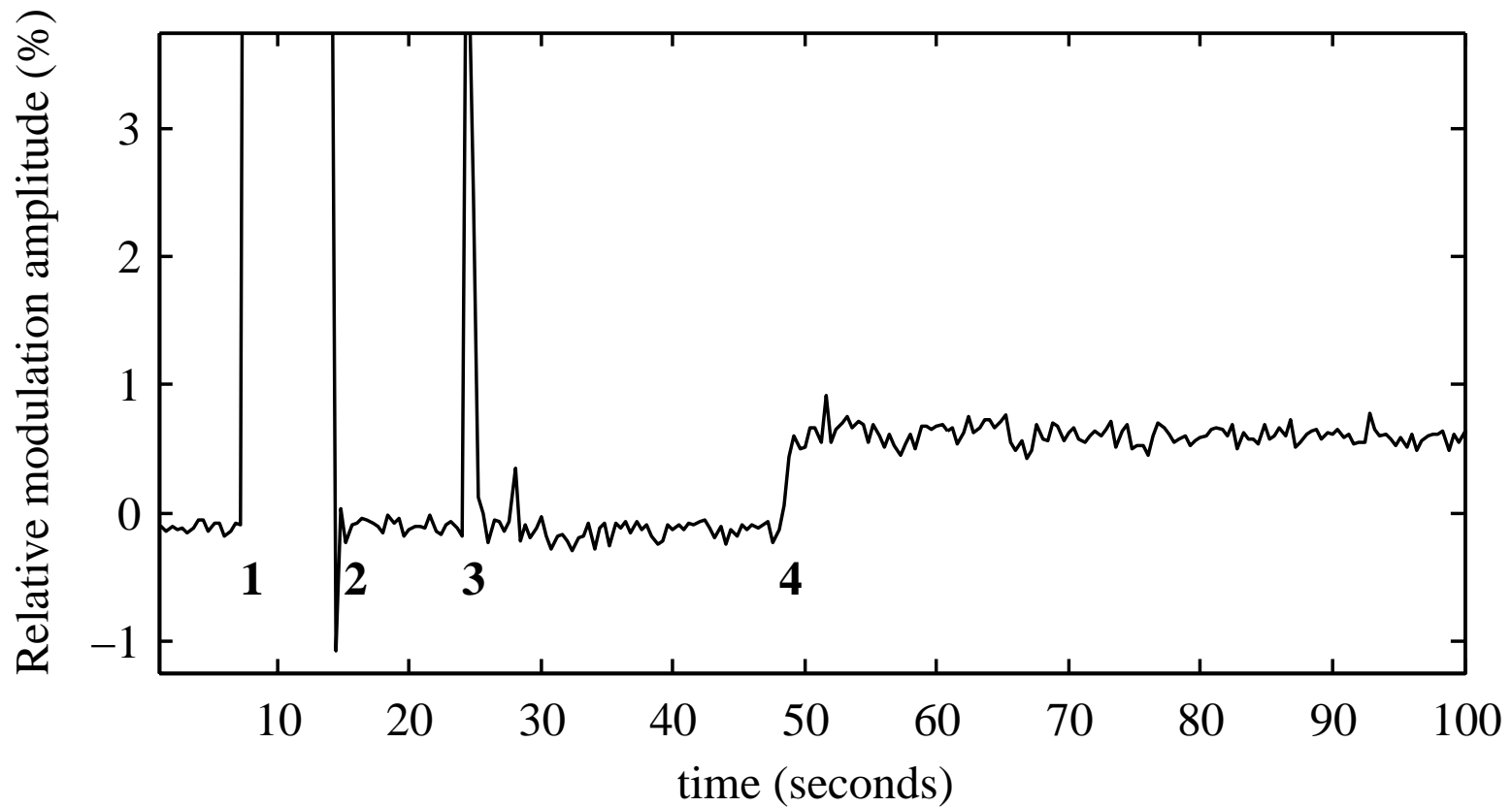


Absorption pattern synthesized by multi-line filter

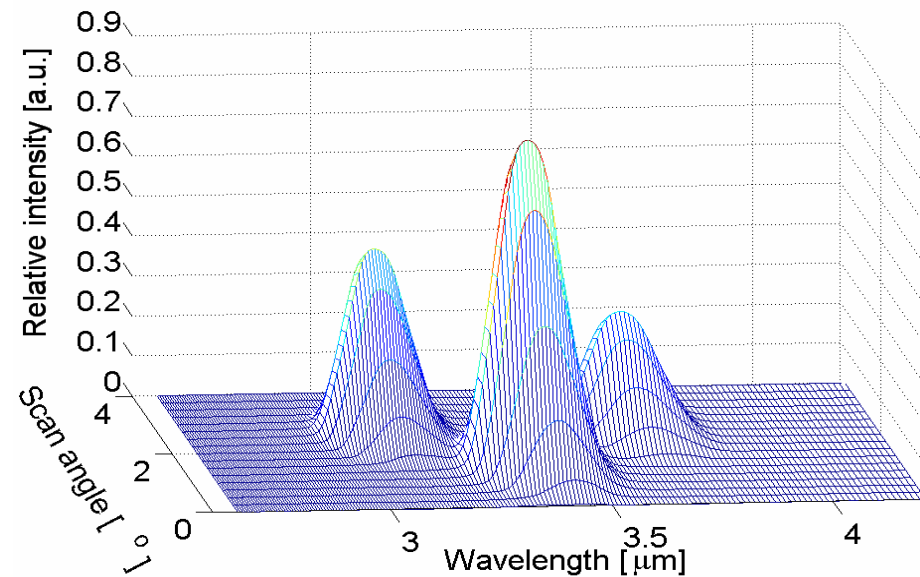
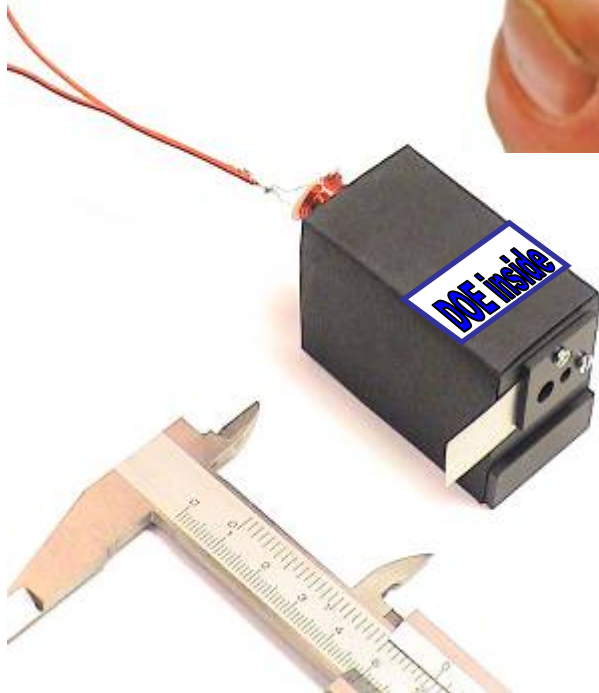
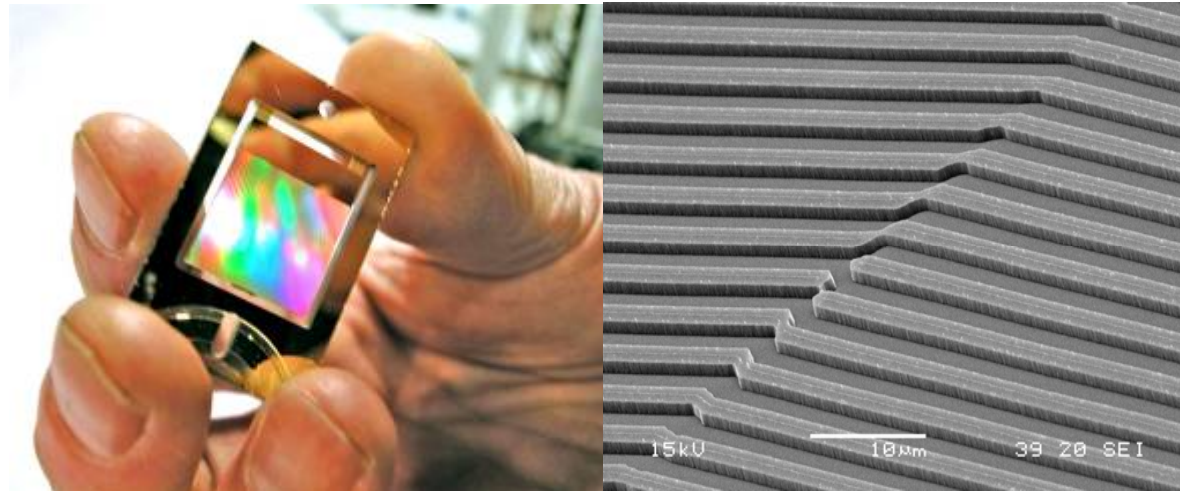




# CO measurements with the slab sensor

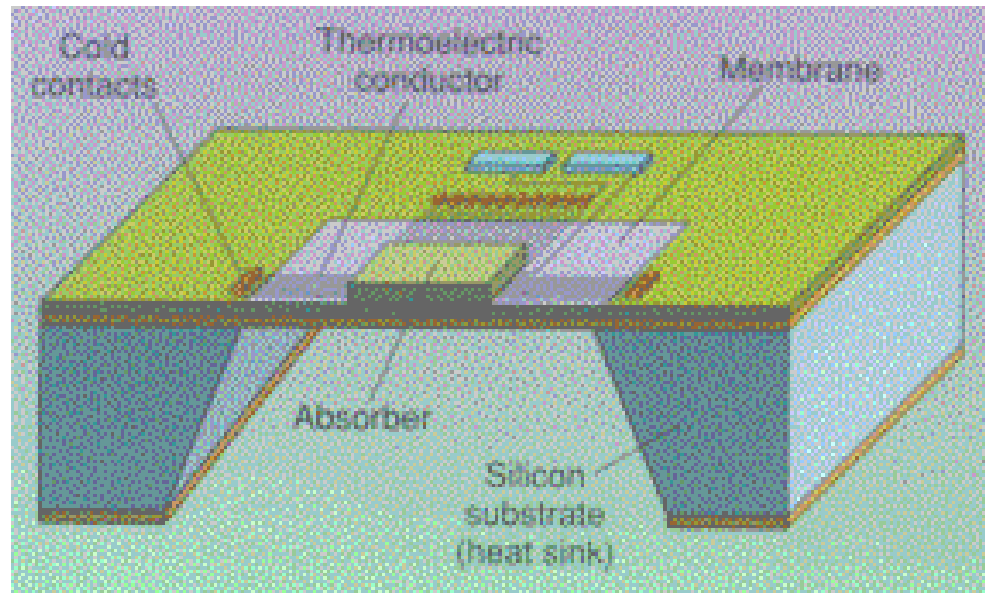


# Diffractive optics for gas sensors



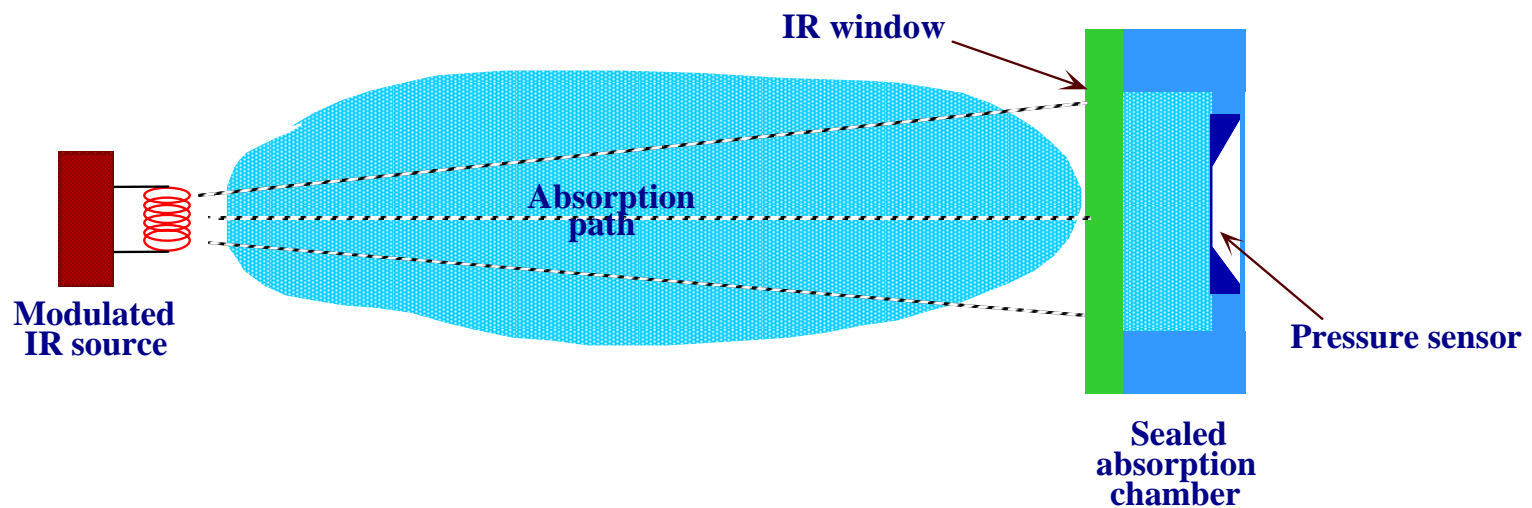
# MEMS based IR detectors

## Thermopile detector

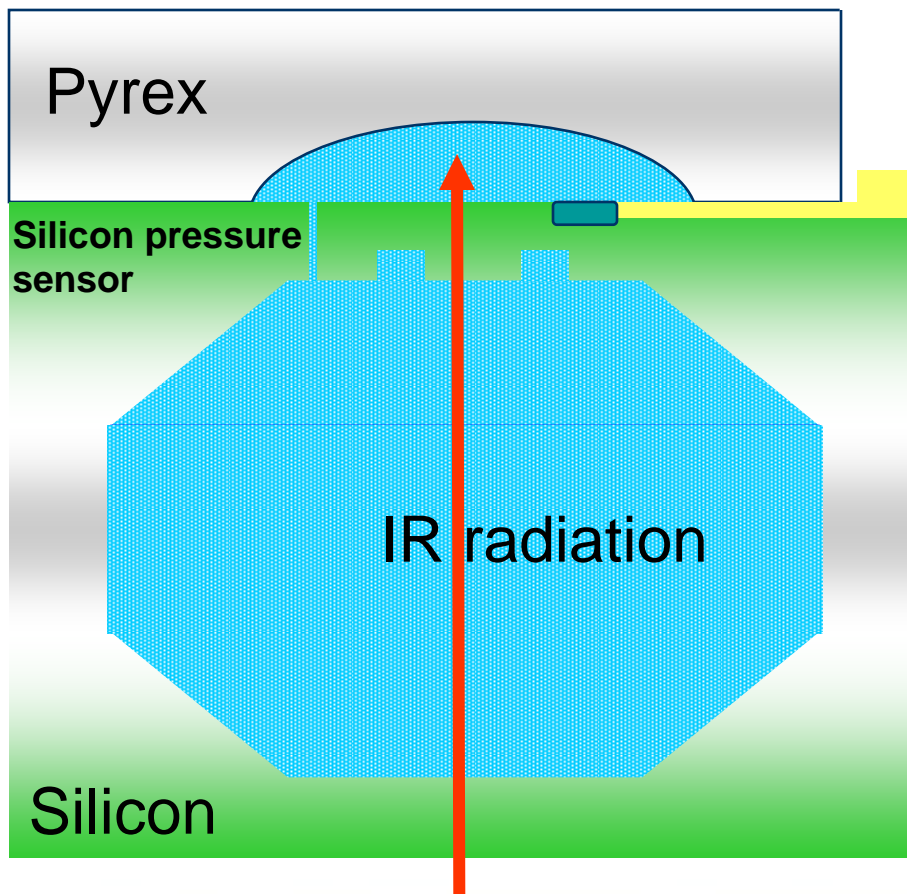


*Wolfgang Schmidt and Jörg Schieferdecker*

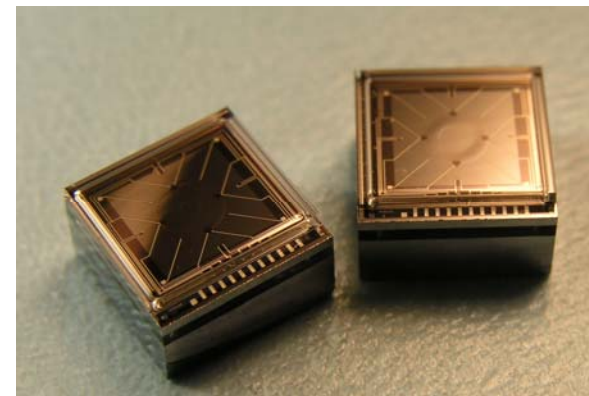
# Filter and detector in one chip: The SINTEF photoacoustic gas sensor



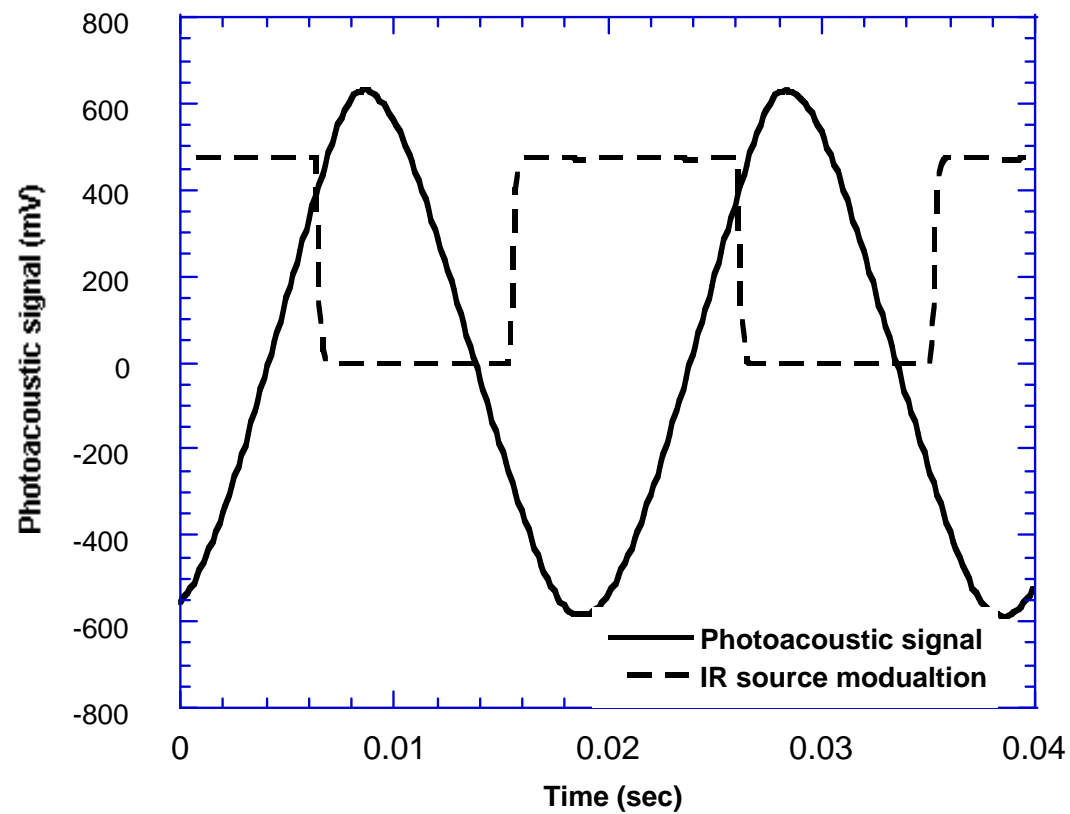
# The photoacoustic detector chip



- Wafer level gas filling
- High precision piezoresistive pressure sensor
- Transferred to the SensoNor MPW foundry process

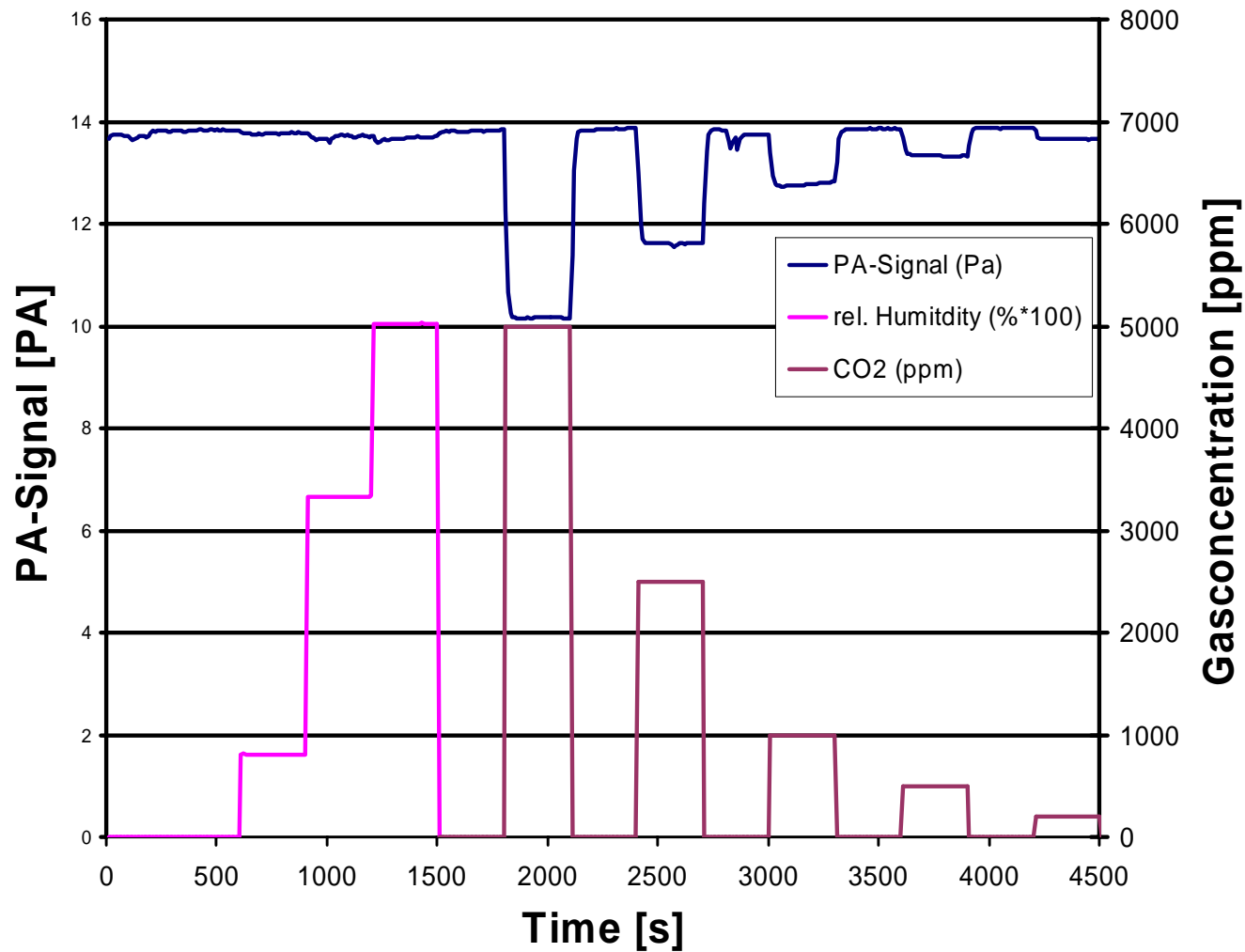


# The photoacoustic signal





# CO<sub>2</sub> Measurement with the PA sensor:



200-100 ppm resolution

# Characteristics

- High selectivity without additional filters
- High sensitivity => small size
- No pumps and valves
- Easily implemented in MEMS technology  
=> low cost
  
- High volume production an packaging technology required
- Long term drift compensation has to be implemented



# MASCOT: Micro-Acoustic Sensors for CO<sub>2</sub> Tracking

Per Gerhard Gløersen, SensoNor AS  
Bertil Hök, Hök Instrument AB  
Niels Peter Østbø, SINTEF



The MASCOT project was co-financed by the IST programme of the European Commission under grant number IST-2001-32411

# Electro-acoustic IAQ sensor



# Device modelling basics

Relationship between velocity of sound  $c$  and molecular mass  $M$  of a gas:

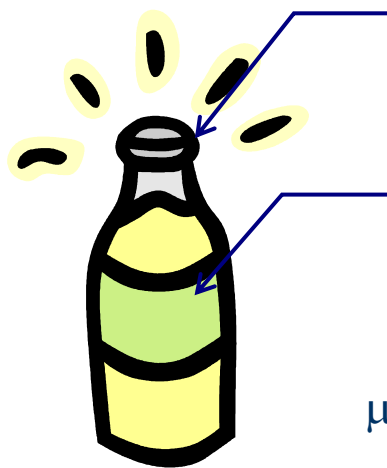
$$c = \sqrt{\frac{RT\gamma}{M}}$$

$R$ : universal gas constant (=8.314 J/mol K),

$T$ : absolute temperature (K)

$\gamma$ : Ratio of specific heat at constant pressure and volume

Resonant frequency and  $Q$  of a Helmholtz resonator:



Neck effective length  $l$   
and area  $A$  (radius  $a$ )

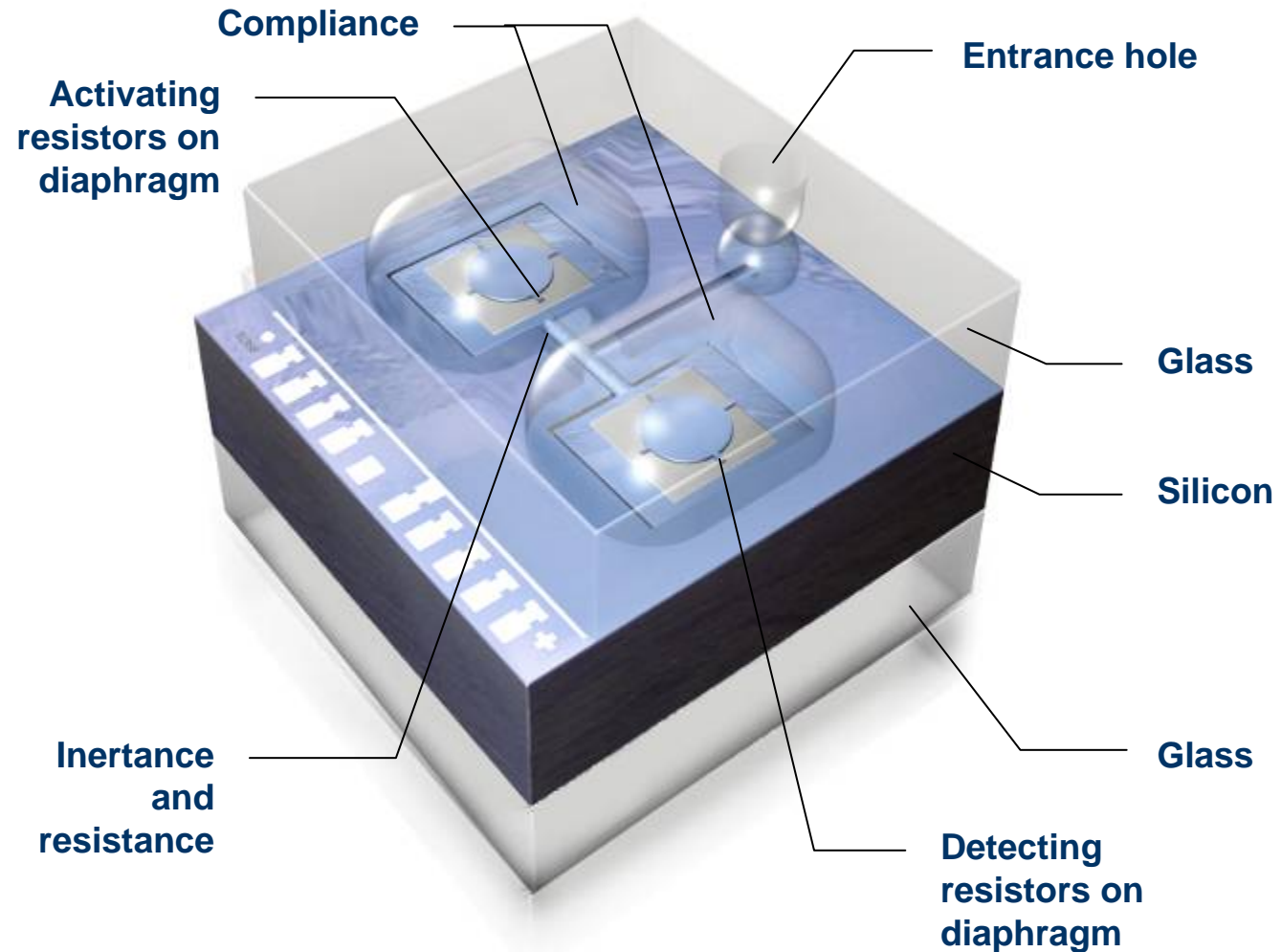
Compliant gas  
volume  $V$

$\mu$ : kinematic viscosity of gas

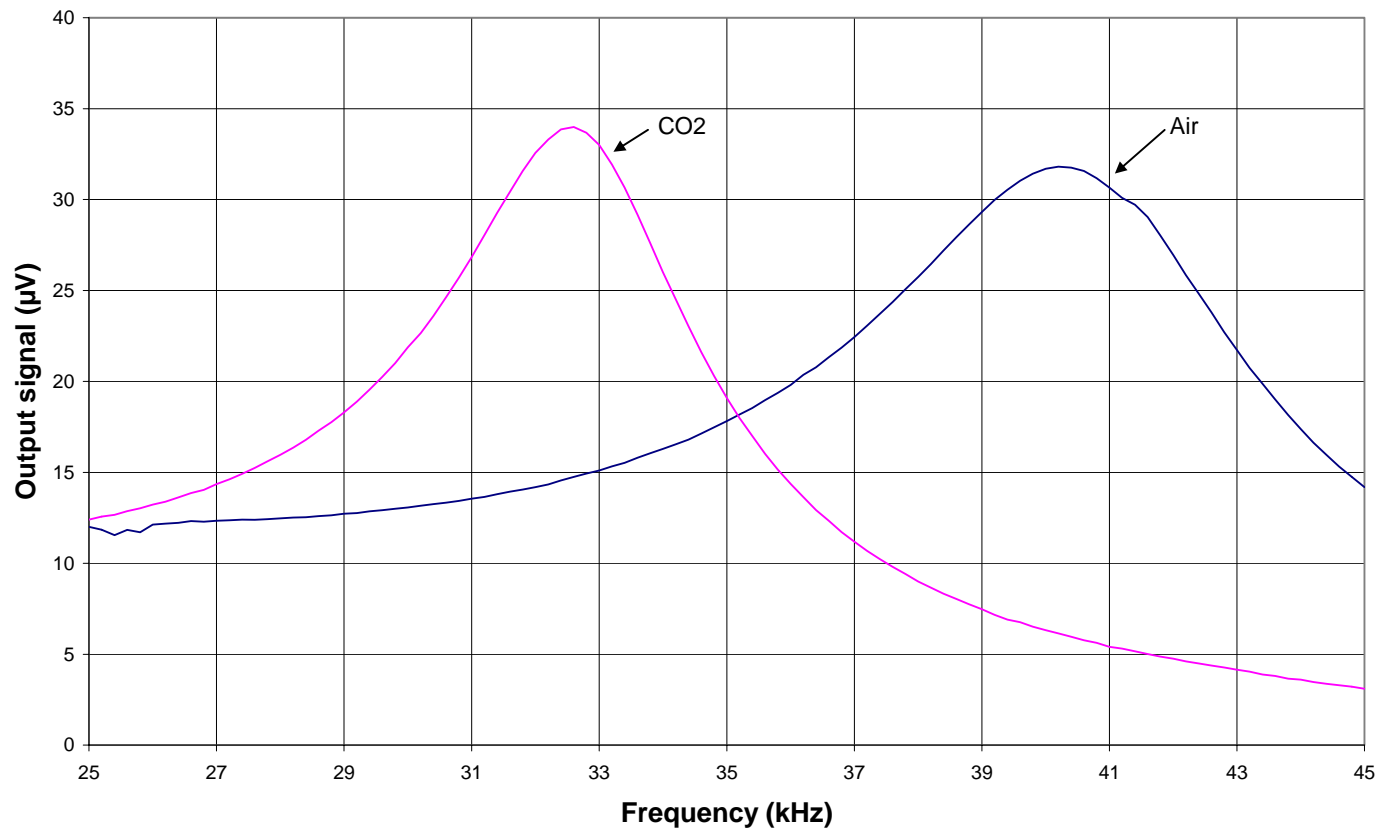
$$f_r = \frac{c}{2\pi} \sqrt{\frac{A}{\ell \cdot V}}$$

$$Q \approx a \cdot \sqrt{\frac{\omega_r}{2\mu}}$$

# Schematic drawing of sensor chip



# Sensor output signal in air and CO<sub>2</sub>

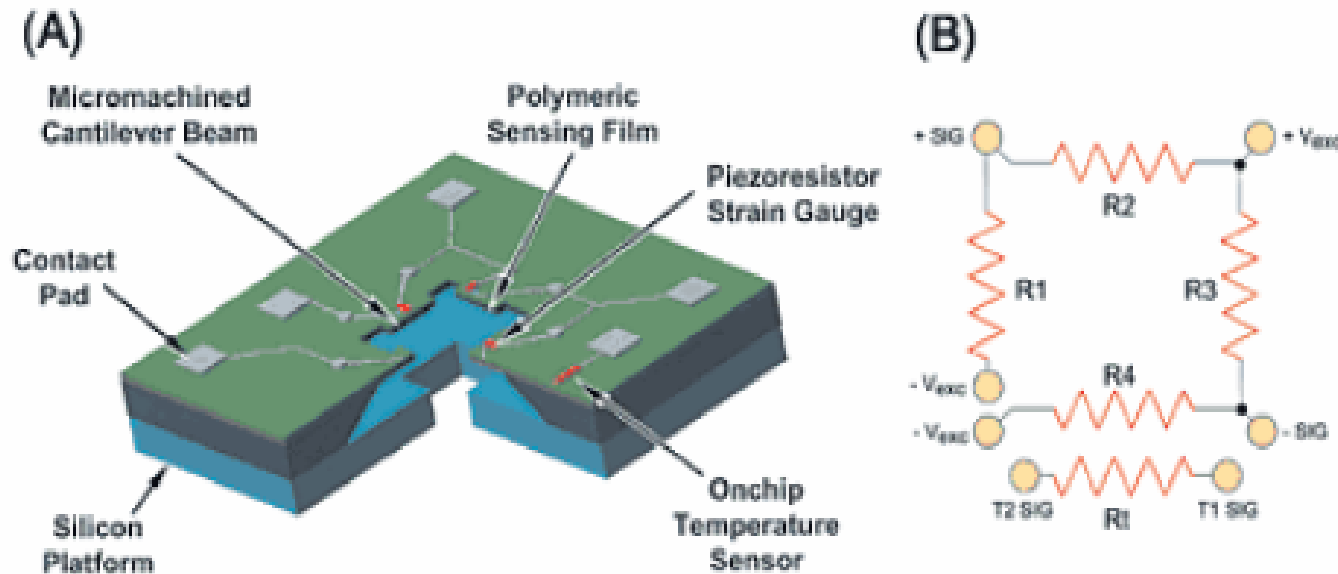


The resonance frequency shifts from 40 to 32 kHz and the Q factor increases from 6.5 to 8.1

# Sensor characteristics

	$f_r$	$Q$
<i>Typical value</i>	40250 Hz	6.60
<i>CO<sub>2</sub></i>	-11 Hz/1000ppm	+0.009/1000ppm
<i>RH</i>	+4 Hz/%RH	-0.001/%RH
<i>Temp</i>	63 Hz/°C	-0.015/°C
<i>Pressure</i>	0	+0.04/kPa
<i>Resolution</i>	±2 Hz (±200 ppm CO <sub>2</sub> or ±0.5% RH)	±0.01

# MEMS based humidity sensors



Die Size: 2 mm x 2 mm

Figure 3. The HMX2000, a silicon-based RH sensor, contains a full Wheatstone bridge circuit and a temperature sensor on a single chip (A). The circuitry is shown for the devices on the sensor chip (B).

# Some aspects of multi sensors

- The challenge is often NOT to be sensitive to humidity and temperature
- Temperature sensors are easily implemented as an integral part of standard electronics.
- Multi sensors are often based on MCM integration.
- MEMS devices is potential easy to integrate since the are small and often based on the same principles (piezoresistive, capacitive and optical)
- MEMS also opens for a higher degree monolithic integration
  - Temperature sensors as part of the gas sensor chip



# Conclusion

- IR technology offers highly sensitive, selective and reliable gas sensors.
- MEMS based IR sources, IR detectors, tuneable optical filters, and complete gas and humidity sensors are available.
- IR gas sensors are, however, still expensive due to large size, expensive components, packaging, and drift compensation. Higher level of integration is required.
- A DOE based CO<sub>2</sub> under industrialization by Optosene AS
- A MEMS based photo-acoustic gas sensor for CO<sub>2</sub> is demonstrated offering high selectivity, sensitivity, and is compatible with MEMS technology.
- A new class of electro-acoustic MEMS-implemented CO<sub>2</sub> sensors has been demonstrated:
  - Simple and uncritical geometry
  - Strong potential for mass-production at low cost
- A CO sensor based on a thermally tuned F-P filter is demonstrated. The detection limit for CO was 20 ppm•m, and 50 ppm•m for methane.
- MEMS based sensors are by their small size and fabrication and packaging technology potentially suitable for multi-sensor integration